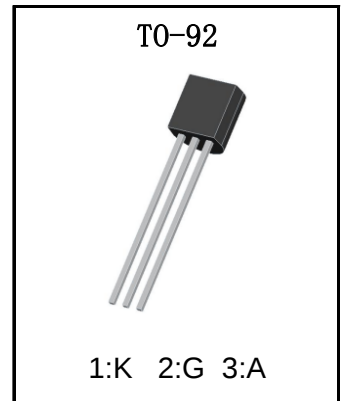


Features

Repetitive Peak Off-State Voltage : 400

R.M.S On-State Current ($I_T(\text{RMS})=0.8\text{A}$)

Low On-State Voltage (1.3V(Typ))



Maximum ratings($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Repetitive peak off-state voltage	VDRM	400	V
Repetitive peak reverse voltage	VRRM	400	V
RMS on-state current (full sine wave)	$I_T(\text{RMS})$	0.8	A
Non-repetitive peak on-state current	I_{TSM}	8	A
Peak gate power dissipation	PGM	0.5	W
Operating junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~150	$^\circ\text{C}$

Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Repetitive peak off-state voltage	VDRM	$I_{DRM}=10\mu\text{A}$	400			V
Repetitive peak reverse voltage	VRRM	$I_{RRM}=10\mu\text{A}$	400			V
Maximum forward leakage current	I_{DRM}	$V_{DRM}=400\text{V}$			10	μA
Maximum reverse leakage current	I_{RRM}	$V_{RRM}=400\text{V}$			10	μA
Holding current	I_H	$V_d=12\text{V}$ $I_T=50\text{mA}$			5	mA
On-state voltage	V_{TM}	$I_T=0.8\text{A}$			1.7	V
Gate trigger voltage	V_{GT}	$V_d=12\text{V}$			1.2	V
Gate trigger current	I_{GT}	$V_d=12\text{V}$			120	μA
Critical Rate of Rise On-State Voltag	di/dt	$I_{pk}=2\text{A}$, $I_{GT}=20\text{mA}$			50	A/ μS
Critical Rate of Rise Off-State Voltag	dv/dt	$V_D=0.67V_{DRM}$, $T=110^\circ\text{C}$	20			V/ μS

Typical Characteristics

